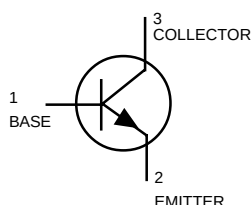
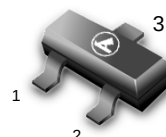


Low Noise Transistor

NPN Silicon



MMBT2484LT1



CASE 318-08, STYLE 6
SOT-23 (TO-236AB)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBT2484LT1 = 1U

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	60	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 45\text{Vdc}, I_E = 0$)	I_{CBO}	—	10	nAdc
($V_{CB} = 45\text{Vdc}, I_E = 0, T_A = 150^\circ\text{C}$)		—	10	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	10	nAdc

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MMBT2484LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

ON CHARACTERISTICS

DC Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 5.0V _{dc})	h _{FE}	250 —	— 800	—
Collector–Emitter Saturation Voltage (I _C = 1.0 mA _{dc} , I _B = 1.0 mA _{dc})	V _{CE(sat)}	—	0.35	V _{dc}
Base–Emitter On Voltage (I _C = 1.0 mA _{dc} , I _{CE} = 5.0 mA _{dc})	V _{BE(on)}	—	0.95	V _{dc}

SMALL–SIGNAL CHARACTERISTICS

Output Capacitance (V _{CB} = 5.0 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	—	6.0	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	—	6.0	pF
Noise Finure (V _{CE} = 5.0 V _{dc} , I _C = 10 μA _{dc} , R _S = 10 kΩ, f = 1.0 MHz, BW = 200 Hz)	NF	—	3.0	dB

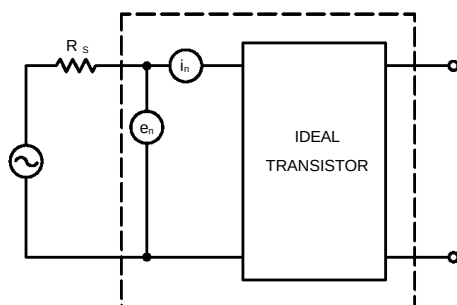


Figure 1. Transistor Noise Model

MMBT2484LT1

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

NOISE VOLTAGE

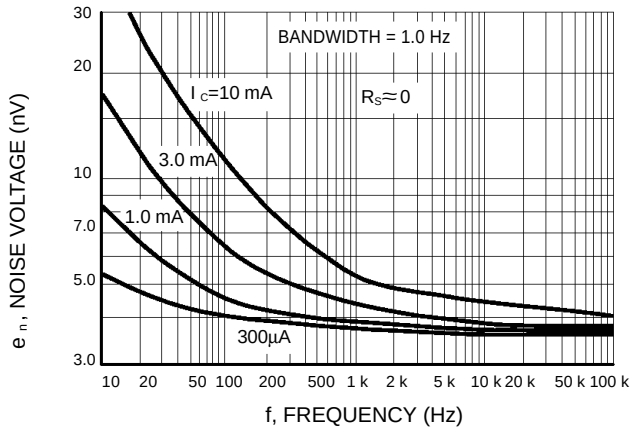


Figure 2. Effects of Frequency

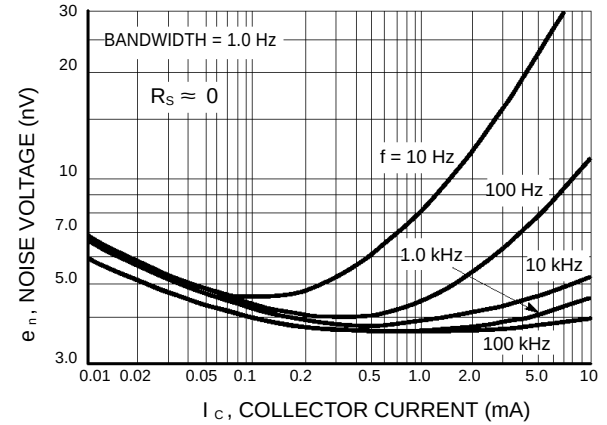


Figure 3. Effects of Collector Current

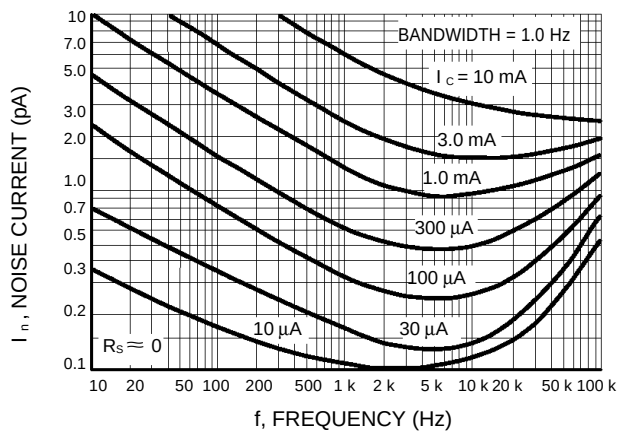


Figure 4. Noise Current

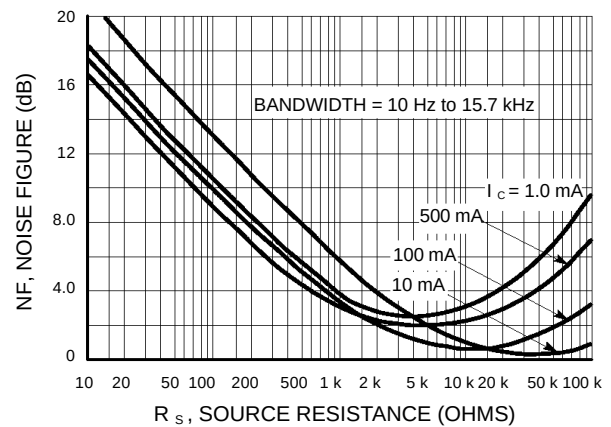


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA

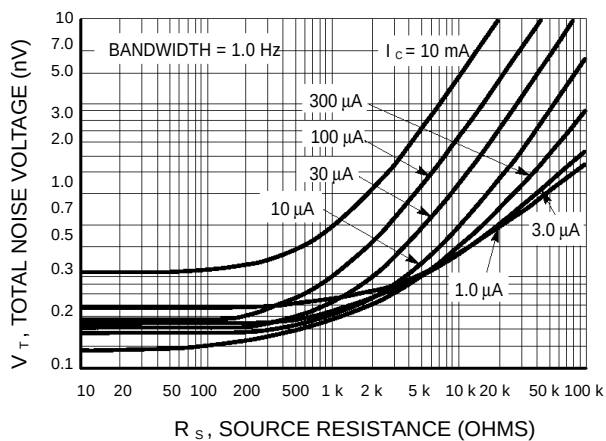


Figure 6. Total Noise Voltage

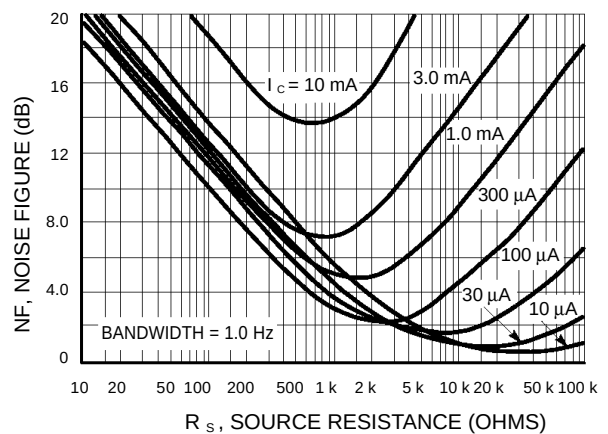


Figure 7. Noise Figure

MMBT2484LT1

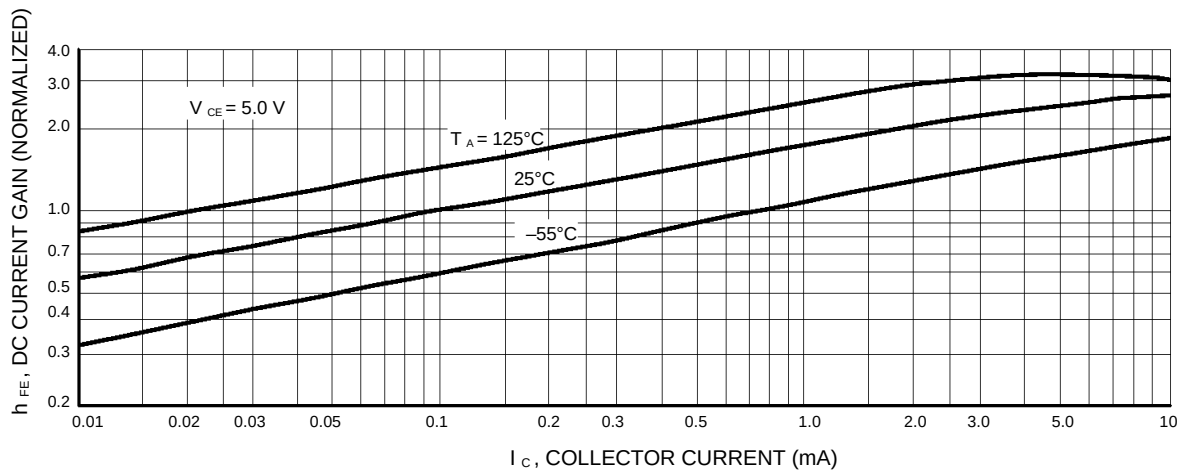


Figure 8. DC Current Gain

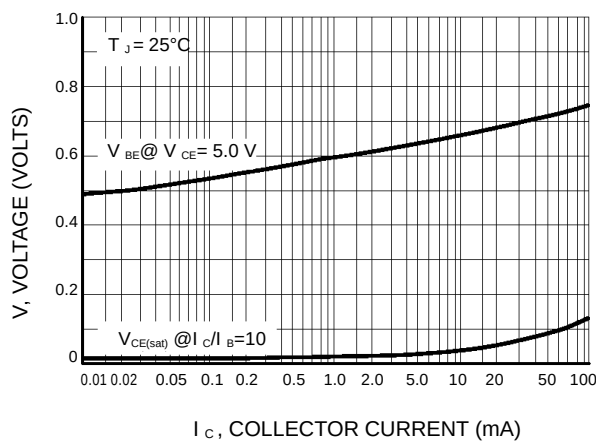


Figure 9. "On" Voltages

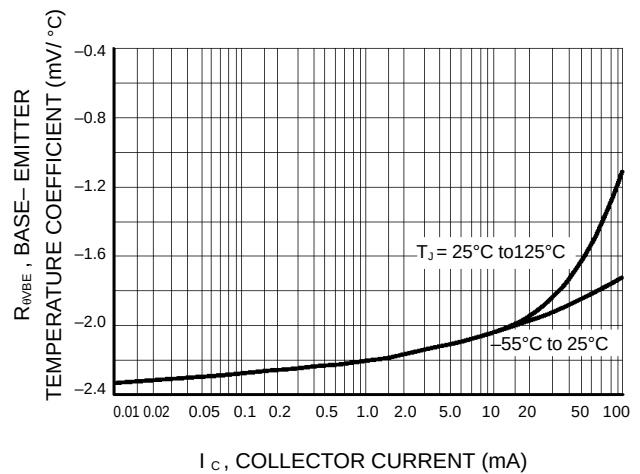


Figure 10. Temperature Coefficients

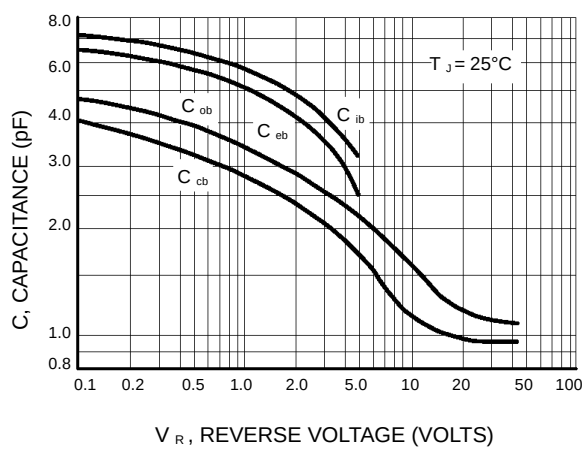


Figure 11. Capacitance

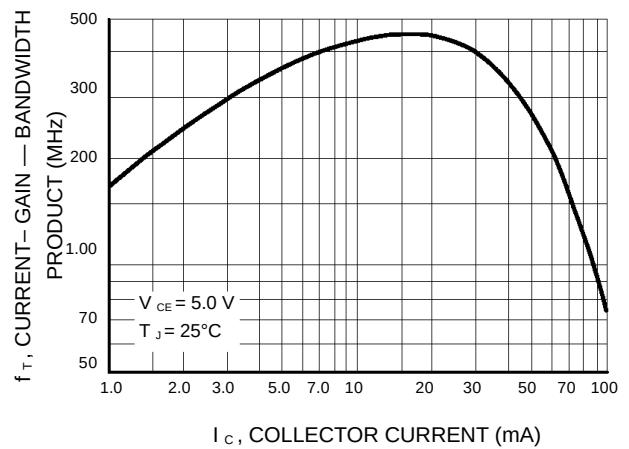


Figure 12. Current-Gain — Bandwidth Product